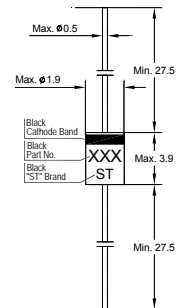


# 1N914, 1N914A, 1N914B

## Silicon Epitaxial Planar Switching Diode

### Features

- Fast switching speed
- High reliability



Glass Case DO-35  
Dimensions in mm

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	$V_{RM}$	100	V
Reverse Voltage	$V_R$	75	V
Average Rectified Forward Current	$I_{F(AV)}$	75 200	mA
Forward Continuous Current	$I_{FM}$	150 300	mA
Non-Repetitive Peak Forward Surge Current	$I_{FSM}$	1 1 4	A
Power Dissipation	$P_{tot}$	500	mW
Operating and Storage Temperature Range	$T_j, T_{stg}$	- 65 to + 175	$^\circ\text{C}$

### Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage	$V_F$	0.62	0.72	V
at $I_F = 5\text{ mA}$				
at $I_F = 100\text{ mA}$		-	1	
at $I_F = 10\text{ mA}$		-	1	
at $I_F = 20\text{ mA}$		-	1	
Reverse Current	$I_R$	-	25	nA
at $V_R = 20\text{ V}$				
at $V_R = 75\text{ V}$			5	$\mu\text{A}$
at $V_R = 20\text{ V}, T_j = 150^\circ\text{C}$			50	$\mu\text{A}$
Diode Capacitance	$C_j$	-	4	pF
at $V_R = 0, f = 1\text{ MHz}$				
Reverse Recovery Time	$t_{rr}$	-	4	ns
at $I_F = 10\text{ mA}$ to $I_R = 1\text{ mA}, V_R = 6\text{ V}, R_L = 100\ \Omega$				